



- Low forward voltage and leakage current
- Low inductance package
- High surge current capability

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(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Peak forward voltage	$I_F=50\text{A}$, $t_P=380\mu\text{s}$	V_{FM}		1.20	1.40	V
Reverse leakage current	$V_R = V_{RRM}$, $T_{vj} = 25$	I_{RRM}			0.2	mA
	$V_R = V_{RRM}$, $T_{vj} = 150$				3	mA
Threshold voltage	$T_{vj} = 150$, for power loss calculation only	V_{TO}			0.95	V
Dynamic resistance		r_T			7.0	mΩ

(@ $T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Thermal resistance, junction to case	per diode	$R_{th(j-c)}$			1.5	K/W
Thermal resistance, case to heatsink	per module	$R_{th(c-s)}$			0.2	K/W
Mounting torque	Module and heatsink fixed torque	M	2.5		3.5	N m

JMD50TD18D0	JMD50TD18D0	D0	78g/PCS	28PCS	140PCS

FIG.1: Forward characteristics(per diode)

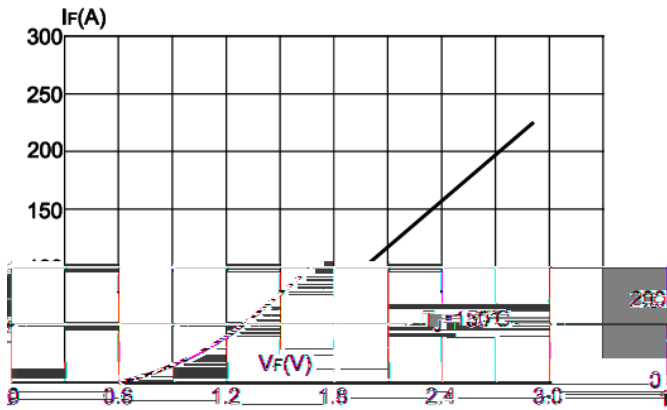
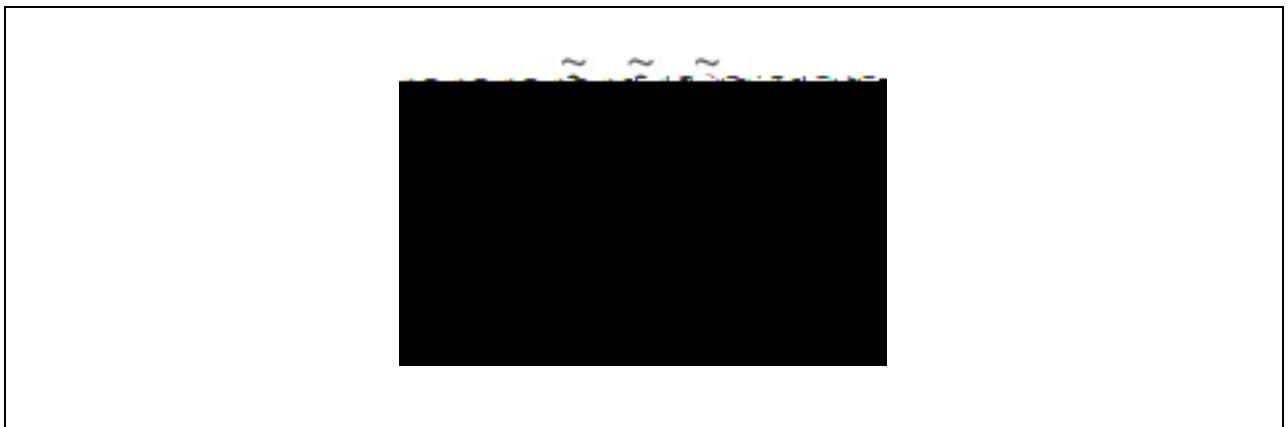
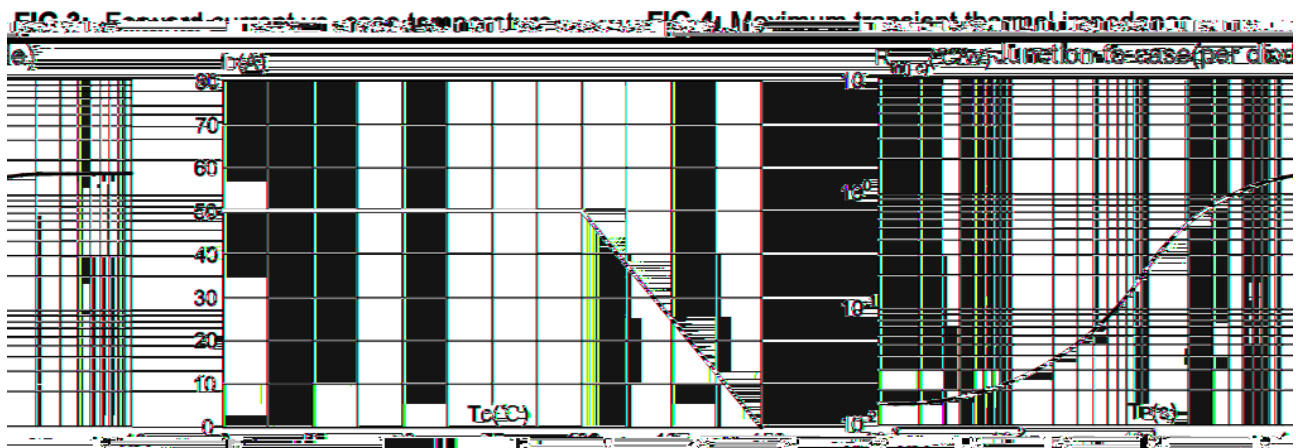
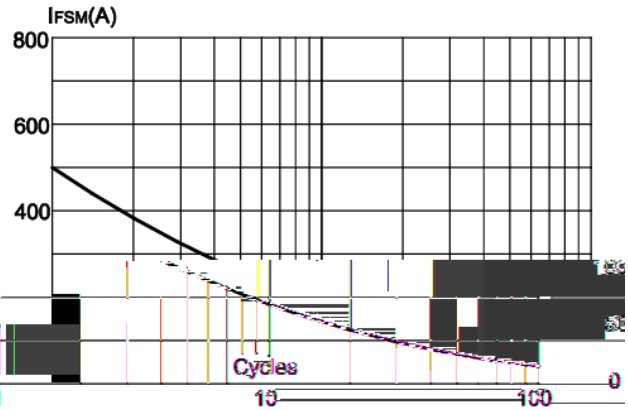
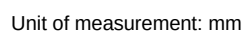


FIG.2: Peak on-state surge current







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